IN THE CLAIMS:

Please cancel claims 1-21 without prejudice and add new claims 22-38 as shown in the following list of claims:

1-21. (Cancelled)

22. (New) A method for processing a substrate, comprising:

depositing an electrically conductive seed layer onto a substrate;

immersing the substrate into a plating solution; and

plating metal ions from the plating solution onto the substrate during the immersing process by applying a plating bias to the substrate at a charge density between about 20 mA*sec/cm^2 and about 160 mA*sec/cm^2.

22. (New) The method of claim 22, wherein applying a plating bias to the substrate comprises applying a bias between about 0.8 volts and about 20 volts for a period of time sufficient to compensate for etching of the seed layer by the plating solution during the immersing process.

23. (New) The method of claim 23, wherein the plating bias is applied between about 0.1 seconds and about 4 seconds.

24. (New) The method of claim 22, wherein plating metal ions from the plating solution comprises plating a layer of metal ions onto the seed layer, wherein the layer of metal ions has a thickness of between about 50Å and about 250Å.

25. (New) The method of claim 22, wherein the metal ions comprise at least one of copper, nickel, and tungsten.

26. (New) The method of claim 22, wherein the applying the plating bias comprises applying an increasing plating bias to the substrate during the immersing process.

27. (New) The method of claim 22, wherein the applying the plating bias comprises applying a pulse modulated plating bias to the substrate during the immersion process.

28. (New) The method of claim 22, wherein plating metal ions from the plating solution comprises plating an alloy layer onto the seed layer.

29. (New) A method for electrochemically plating a first metal layer onto a substrate surface having high aspect ratio features formed thereon, comprising:

depositing a seed layer over the substrate surface and features;

immersing the substrate surface and features into an electrochemical plating solution; and

applying a plating bias at a charge density of between about 20 mA*sec/cm^2 and about 160 mA*sec/cm^2 during the immersing process to deposit a first metal layer on the seed layer.

30. (New) The method of claim 29, wherein applying the plating bias comprises applying an increasing plating bias to the substrate during the immersing process or applying a pulse modulated plating bias to the substrate during the immersion process.

31. (New) The method of claim 29, wherein the plating bias is applied for a duration of between about 0.5 seconds and about 2 seconds.

32. (New) The method of claim 29, wherein applying the plating bias comprises applying a bias between about 0.8 volts and about 20 volts to the seed layer for a period of time between about 0.1 second and about 4.0 seconds during the immersing process.

33. (New) The method of claim 29, further comprising plating a second metal layer over the first metal layer via an electrochemical plating process after the seed layer is fully immersed in the electrochemical plating solution.

34. (New) The method of claim 29, wherein the first layer is a metal alloy layer.

35. (New) A method for immersing a substrate into a plating solution, comprising immersing the substrate into the plating solution while simultaneously applying a charge density of between about 20 mA*sec/cm^2 and about 160 mA*sec/cm^2.

36. (New) The method of claim 35, wherein the charge density is applied by applying a plating bias between about 0.8 volts and about 20 volts to the substrate for a period of between about 0.1 seconds and about 4 seconds.

37. (New) The method of claim 35, wherein the plating bias causes the deposition of a patching layer over a seed layer formed onto the substrate during the immersing process.

38. (New) The method of claim 37, wherein the patching layer comprises a metal alloy layer.